

BUZ71A BUZ71AFI

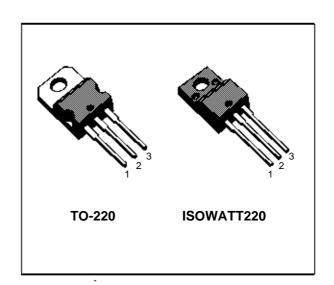
N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTORS

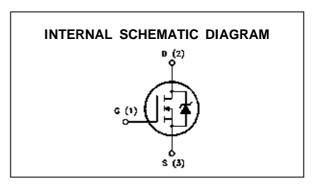
TYPE	V _{DSS}	R _{DS(on)}	ΙD
BUZ71A	50 V	< 0.12 Ω	16 A
BUZ71AFI	50 V	< 0.12 Ω	11 A

- TYPICAL $R_{DS(on)} = 0.1 \Omega$
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- 175°C OPERATING TEMPERATURE

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- REGULATORS
- DC-DC & DC-AC CONVERTERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- AUTOMOTIVE ENVIRONMENT (INJECTION, ABS, AIR-BAG, LAMPDRIVERS, Etc.)





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Val	Value	
		BUZ71A BUZ71AFI		
V _{DS}	Drain-source Voltage (V _{GS} = 0)	5	0	V
V_{DGR}	Drain- gate Voltage ($R_{GS} = 20 \text{ k}\Omega$)	5	0	V
V_{GS}	Gate-source Voltage	± :	20	V
I _D	Drain Current (continuous) at T _c = 25 °C	16 11		Α
I _{DM}	Drain Current (pulsed)	64 64		А
P _{tot}	Total Dissipation at T _c = 25 °C	70	35	W
V _{ISO}	Insulation Withstand Voltage (DC)	_	2000	V
T _{stg}	Storage Temperature	-65 to	175	°C
Tj	Max. Operating Junction Temperature	175		°C
	DIN Humidity Category (DIN 40040)	E		
	IEC Climatic Category (DIN IEC 68-1)	55/15	0/56	

May 1993 1/8

THERMAL DATA

			TO-220	ISOWATT220	
R _{thj-case}	Thermal Resistance Junction-case	Max	2.14	4.29	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5		°C/W

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Value	Unit
lar	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$)	16	А
E _{AS}	Single Pulse Avalanche Energy (starting $T_j = 25$ °C, $I_D = I_{AR}$, $V_{DD} = 25$ V)	50	mJ
E _{AR}	Repetitive Avalanche Energy (pulse width limited by T_j max, δ < 1%)	10	mJ
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive $(T_c = 100 ^{\circ}\text{C}, \text{ pulse width limited by } T_j \text{ max, } \delta < 1\%)$	11	А

ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ ^{o}C unless otherwise specified) OFF

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	$I_D = 250 \mu\text{A}$ $V_{GS} = 0$	50			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	$V_{DS} = Max Rating$ $V_{DS} = Max Rating$ $T_j = 125 ^{\circ}C$			250 1000	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 1 \text{ mA}$	2.1	3	4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 8 A		0.1	0.12	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} = 25 V I _D = 8 A	3	6.5		S
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		330 150 40	450 250 60	pF pF pF

SWITCHING

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
t _{d(on)}	Turn-on Time Rise Time	$V_{DD} = 25 \text{ V}$ $I_D = 8 \text{ A}$ $R_{GS} = 50 \Omega$ $V_{GS} = 10 \text{ V}$		50 100	70 140	ns ns
t _{d(off)}	Turn-off Delay Time Fall Time			40 45	60 65	ns ns



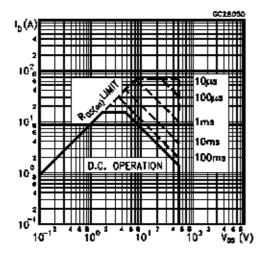
ELECTRICAL CHARACTERISTICS (continued)

SOURCE DRAIN DIODE

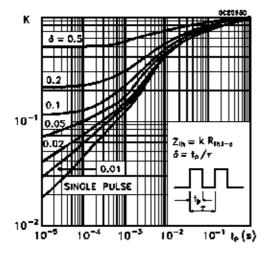
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{SD} I _{SDM}	Source-drain Current Source-drain Current (pulsed)				16 64	A A
V _{SD} (*)	Forward On Voltage	I _{SD} = 32 A V _{GS} = 0			2.2	V
t _{rr}	Reverse Recovery Time	$I_{SD} = 16 \text{ A}$ di/dt = 100 A/ μ s $V_{DD} = 25 \text{ V}$ $T_i = 150 ^{\circ}\text{C}$		70		ns
Q _{rr}	Reverse Recovery Charge	,		0.14		μC

^(*) Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

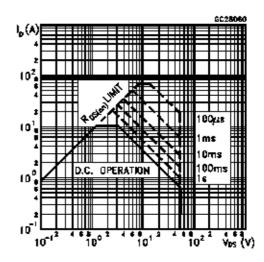
Safe Operating Area For TO-220



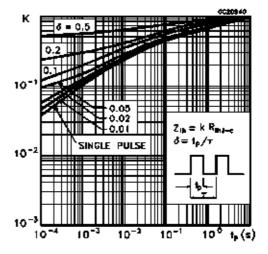
Thermal Impedance For TO-220



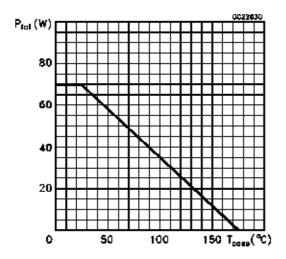
Safe Operating Area For ISOWATT220



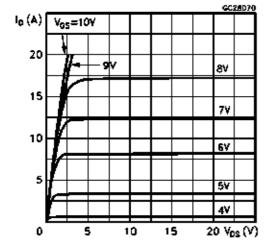
Thermal Impedance For ISOWATT220



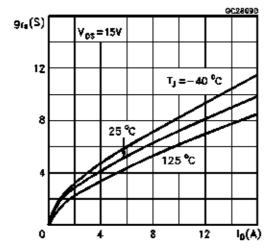
Derating Curve For TO-220



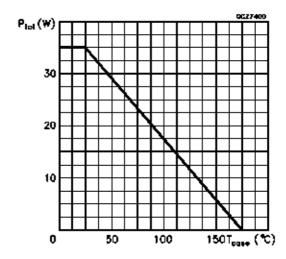
Output Characteristics



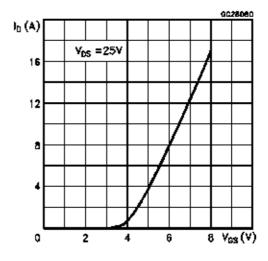
Transconductance



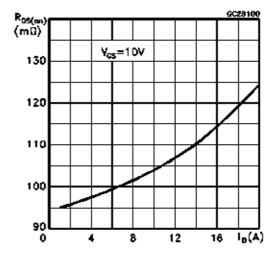
Derating Curve For ISOWATT220



Transfer Characteristics

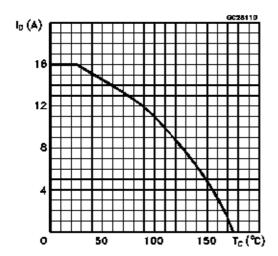


Static Drain-Source On Resistance

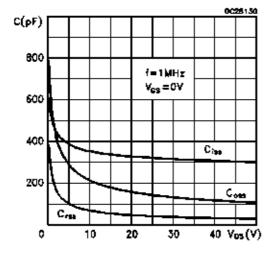


SGS-THOM

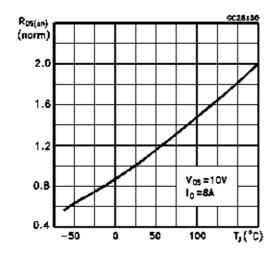
Maximum Drain Current vs Temperature



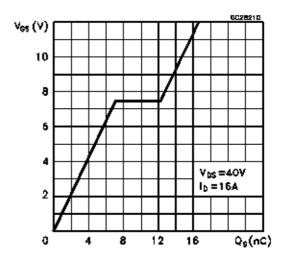
Capacitance Variation



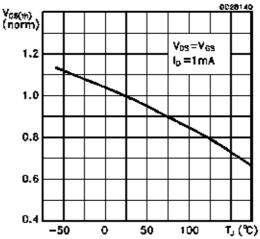
Normalized On Resistance vs Temperature



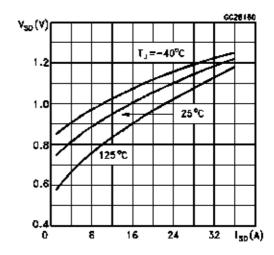
Gate Charge vs Gate-Source Voltage



Normalized Gate Threshold Voltage vs Temperature

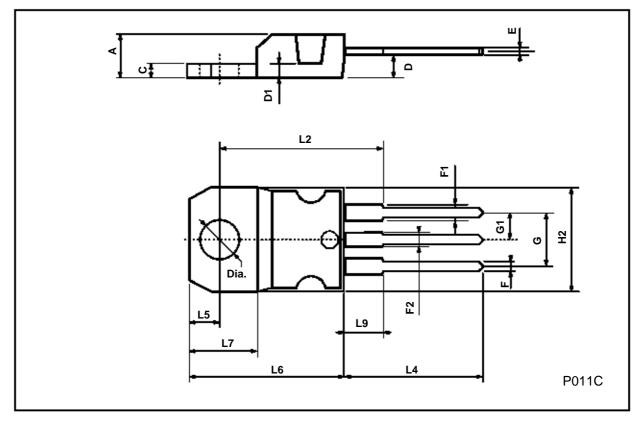


Source-Drain Diode Forward Characteristics



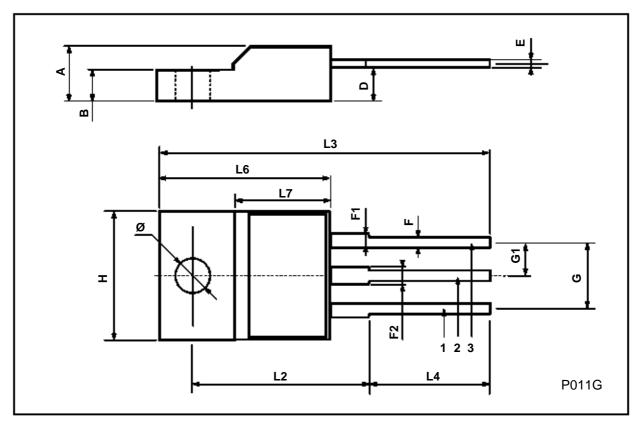
TO-220 MECHANICAL DATA

DIM.		mm			inch	
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	4.40		4.60	0.173		0.181
С	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
Е	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



ISOWATT220 MECHANICAL DATA

DIM.		mm			inch	
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	4.4		4.6	0.173		0.181
В	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.4		0.7	0.015		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
Н	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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